

General Description

The ZM098N06P combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

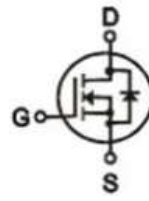
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

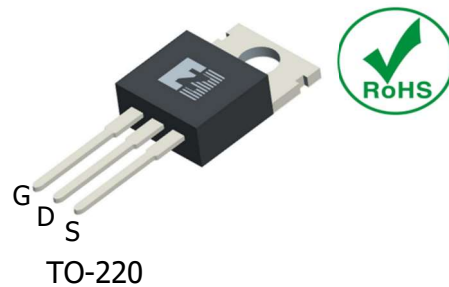
Product Summary



$$V_{DS} = 60V$$

$$R_{DS(ON)} = 11m\Omega$$

$$I_D = 55A$$



Ordering Information:

Part NO.	ZM098N06P
Marking	ZM098N06
Packing Information	Bulk Tube
Basic ordering unit (pcs)	1000

Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current($T_C = 25^\circ C$)	$I_{D@TC=25^\circ C}$	55	A
	$I_{D@TC=75^\circ C}$	42	A
	$I_{D@TC=100^\circ C}$	35	A
Pulsed Drain Current ^①	I_{DM}	104	A
Total Power Dissipation($T_C = 25^\circ C$)	$P_{D@TC=25^\circ C}$	120	W
Total Power Dissipation($T_A = 25^\circ C$)	$P_{D@TA=25^\circ C}$	5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	80	mJ

Avalanche Current@L=0.1mH	I_{AS}	40	A
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•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	25	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=24A$		11	13	m Ω
		$V_{GS}=4.5V, I_D=12A$		14	17	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$		30		s
Source-drain voltage	V_{SD}	$I_S=24A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz VDS=25V	-	3350	-	pF
Output capacitance	C_{oss}		-	155	-	
Reverse transfer capacitance	C_{rss}		-	135	-	

Gate Charge characteristics(Ta= 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	VDD =25V ID = 8A VGS = 10V	-	30	-	nC
Gate - Source charge	Q_{gs}		-	9	-	
Gate - Drain charge	Q_{gd}		-	15	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 SOA Maximum Safe Operating Area

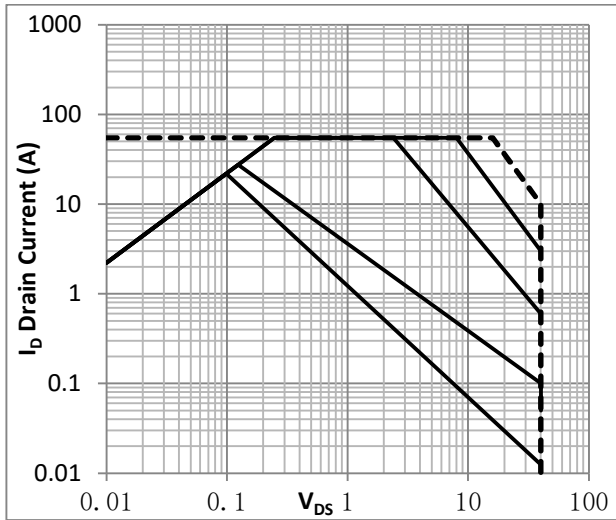


Fig.2 I_D -Junction Temperature

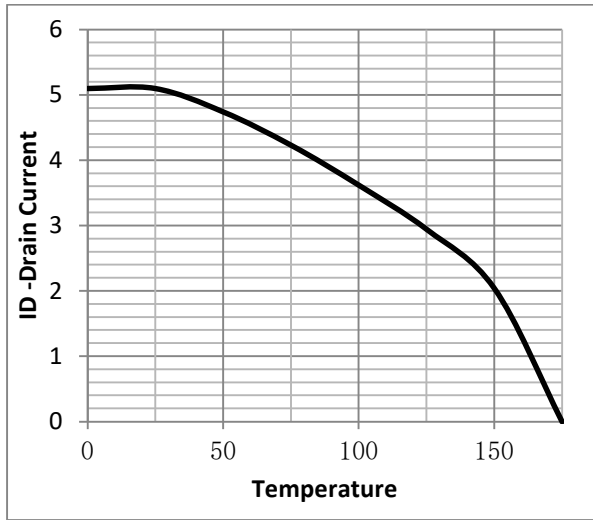


Fig.3 Gate-Charge Characteristics

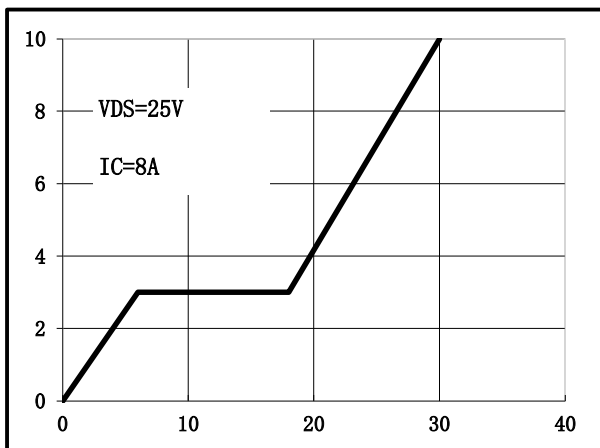


Fig.4 Capacitance Characteristics

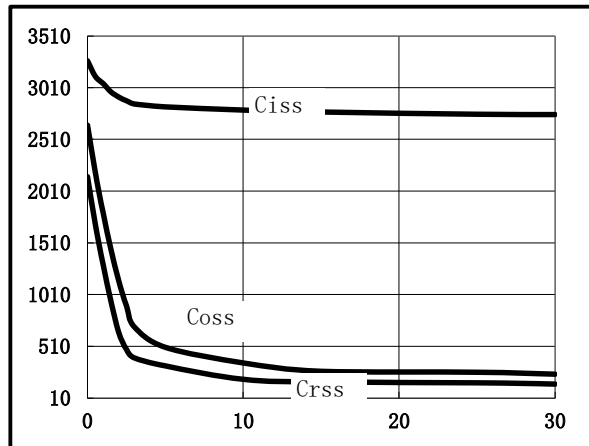


Fig.5 Power Dissipation

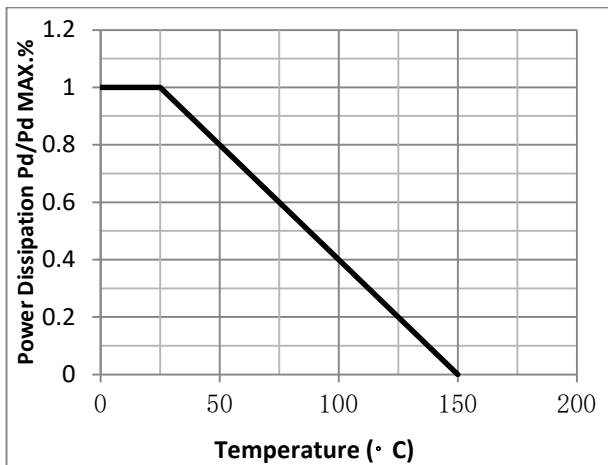


Fig.6 Typical output Characteristics

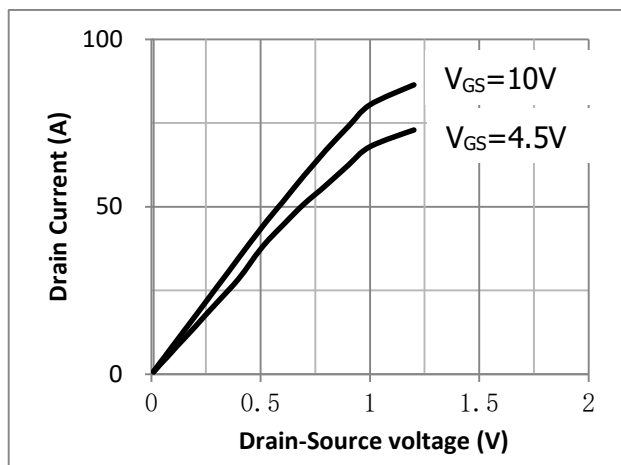


Fig.7 Threshold Voltage V.S Junction Temperature Fig.8 Resistance V.S Drain Current

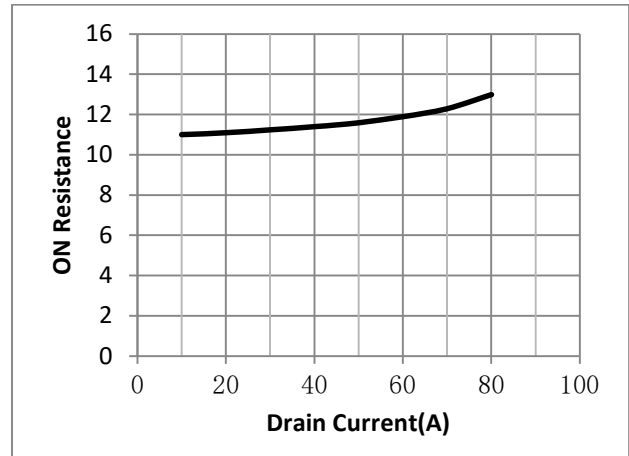
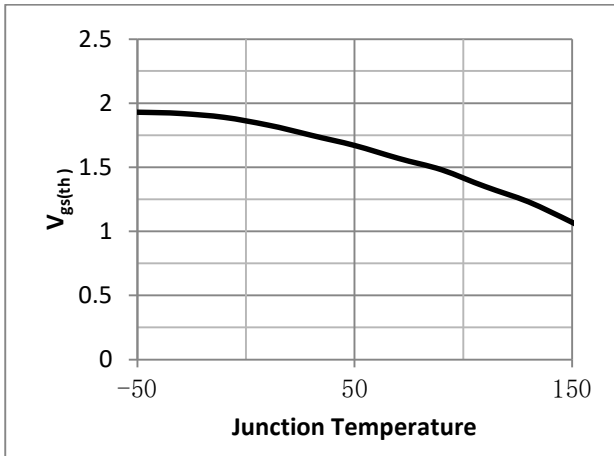


Fig.9 On-Resistance VS Gate Source Voltage

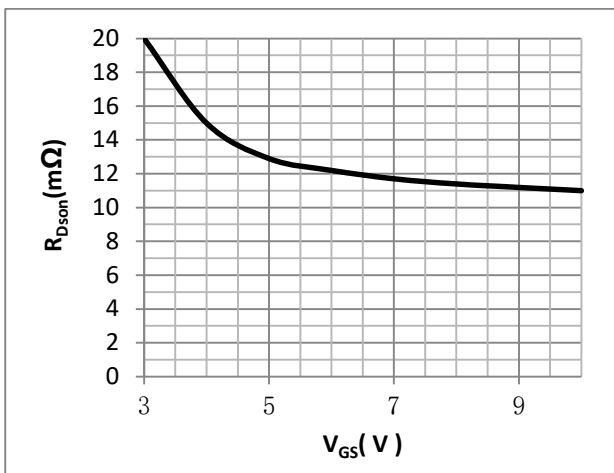


Fig.10 On-Resistance V.S Junction Temperature

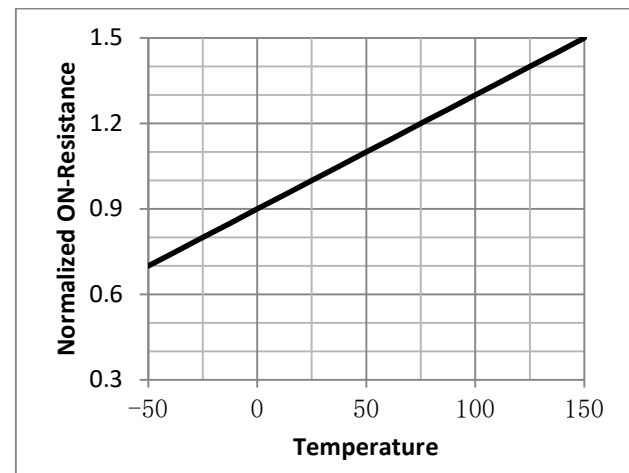


Fig.11 Gate Charge Measurement Circuit

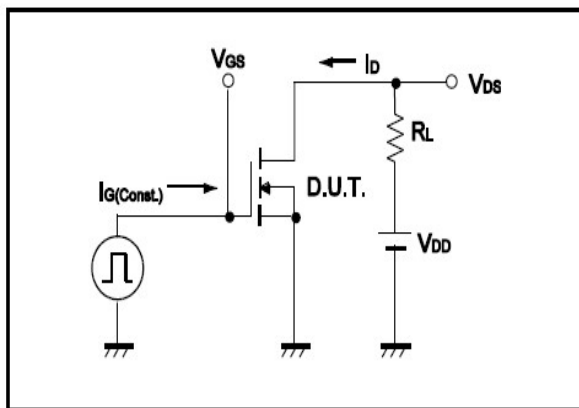


Fig.12 Gate Charge Waveform

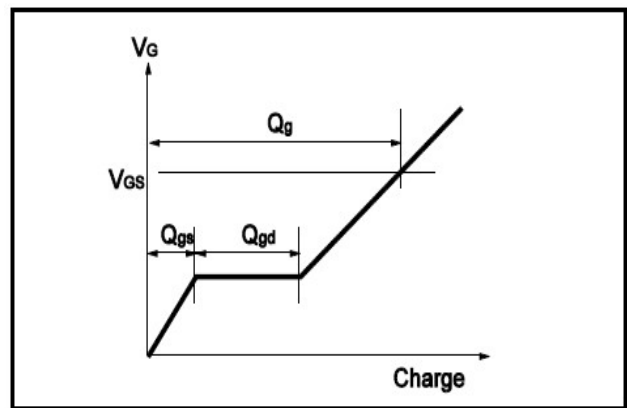


Fig.13 Switching Time Measurement Circuit

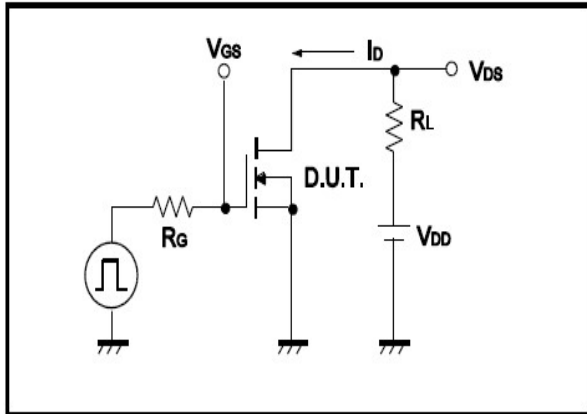


Fig.14 Switching Time Waveform

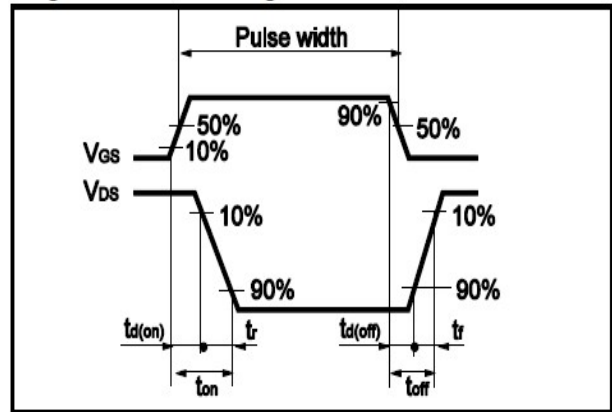


Fig.15 Avalanche Measurement Circuit

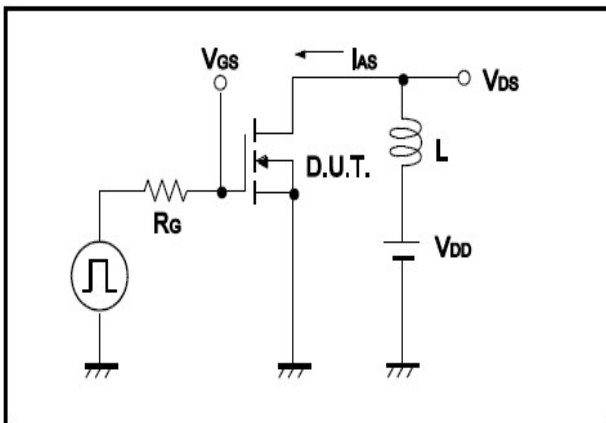
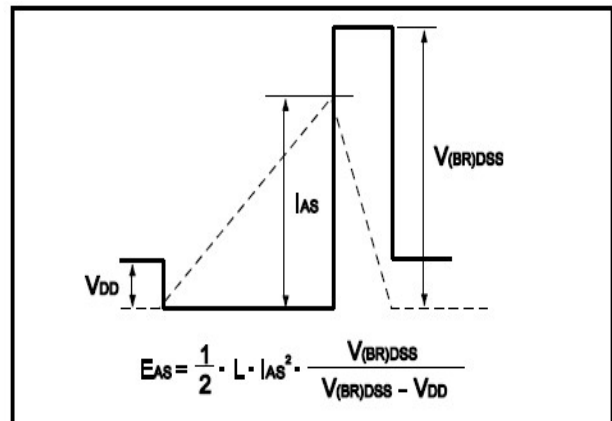


Fig.16 Avalanche Waveform



• **Dimensions (TO-220)**

Unit: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.00		4.80	E	9.90		10.70
B	1.20		1.50	e		2.54	
B1	1.00		1.40	F	1.10		1.45
b1	0.65		1.00	L	12.50		14.50
c	0.35		0.75	L1	3.00	3.50	4.00
D	15.00		16.50	Q	2.50		3.00
D1	5.90		6.90	Q1	2.00		3.00
				ΦP	3.60		3.90

